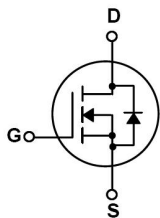


TO-263 N MOS N-CHANNEL MOSFET in a TO-263 Plastic Package.

Low gate charge, Low Crss , Fast switching.

AC/DC

It is very suitable for various AC/DC power conversion in switching mode operation for system miniaturization and higher efficiency.



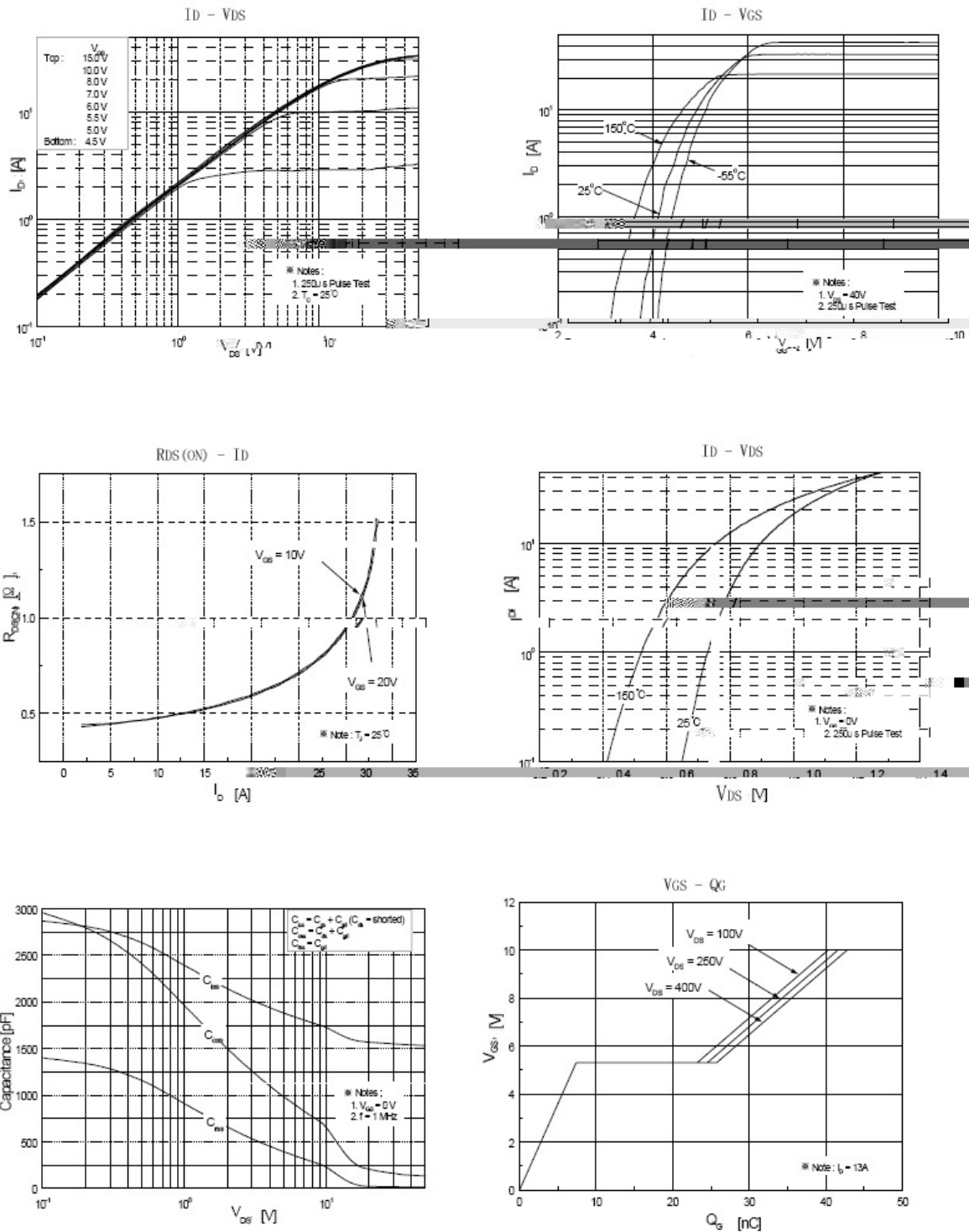
PIN1 G PIN 2,4 D PIN 3 S

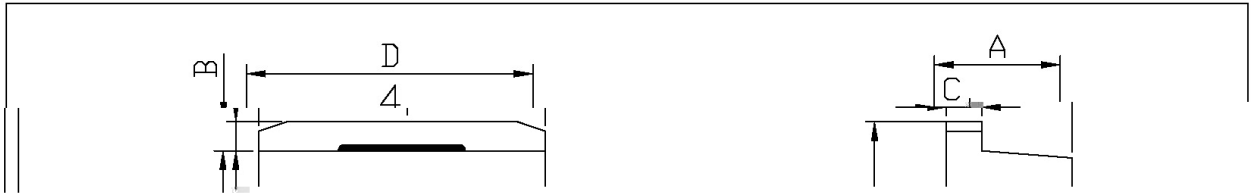
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	500	V
Drain Current	$I_D(T_C=25^{\circ}C)$	13	A
Drain Current	$I_D(T_C=100^{\circ}C)$	8	A
Drain Current - Pulsed	I_{DM}	52	A
Gate-Source Voltage	V_{GSS}	± 30	V
Single Pulsed Avalanche Energy	E_{AS}	860	mJ
Repetitive Avalanche Energy	E_{AR}	19.5	mJ
Avalanche Current	I_{AR}	13	A
Power Dissipation	$P_D(T_C=25^{\circ}C)$	195	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	500			V

Drain-Sou

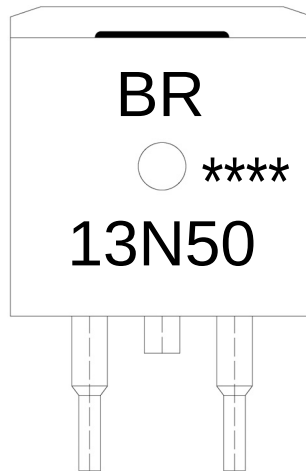




16.00
2.84
1.60

b1	1.15	1.35	L1	15.00
b2	0.40	0.60	L2	2.24
C	1.20	1.40	L3	1.20
D	9.80	10.20		

TP-263



BR

13N50

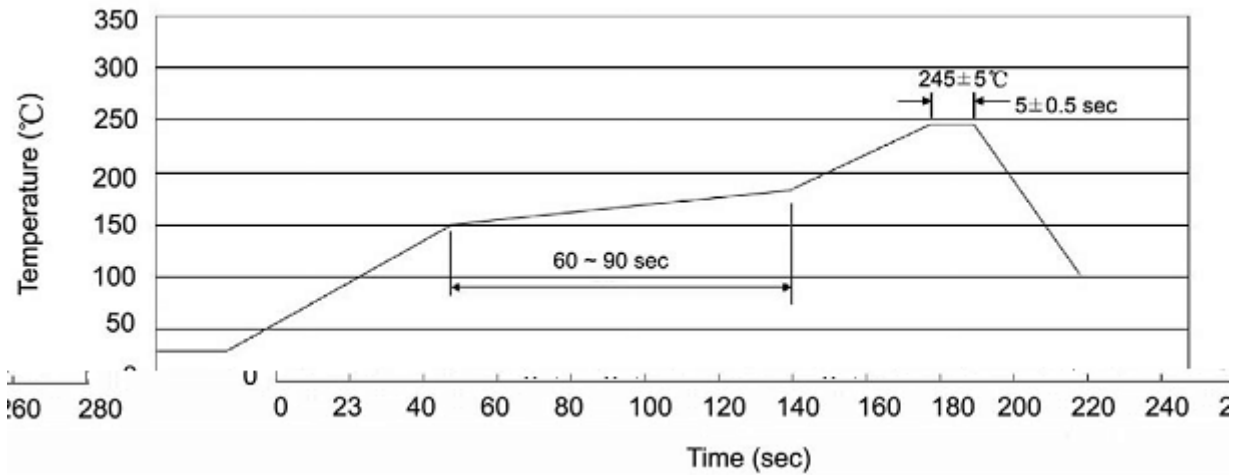
Note:

BR: Company Code

13N50: Product Type.

****: Lot No. Code, code change with Lot No.

Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-------|-----|-----------|--------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 245±5 | | 5±0.5sec; | | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

260±5

10±1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
TO-263	800	1	800	5	4,000	13" ×24	360×360×50	385×257×392

/ TUBE

Package Type	Units					Dimension (unit mm ³)		
	Units/Tube /	Tubes/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Tube	Inner Box	Outer Box
TO-263	50	20	1,000	5	5,000	532×33×7.0	555×164×50	575×290×180